

1 ABSTRACT OF THE DISCLOSURE

2 A chemical-mechanical polishing (CMP) method includes applying
3 a solid abrasive material to a substrate, polishing the substrate,
4 flocculating at least a portion of the abrasive material, and removing at
5 least a majority portion of the flocculated portion from the substrate.
6 Applying solid abrasive material can include applying a CMP slurry or
7 a polishing pad comprising abrasive material. Such a method can further
8 include applying a surfactant comprising material to the substrate to
9 assist in effectuating flocculation of the abrasive material. Such
10 surfactant comprising material may be cationic which includes, for
11 example, a quaternary ammonium substituted salt. Also, for example,
12 the surfactant comprising material may be applied during polishing, brush
13 scrubbing, pressure spraying, or buffing.